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TFE4188 - Introduction to Lecture 2 ICs and ESD

Goal

Understand the **real-world** constraints on our IC

Understand why you must always handle ESD on an IC

The real world constrains our IC

Q: What blocks must our IC include?





Electrostatic Discharge

If you make an IC, you must consider Electrostatic Discharge (ESD) Protection circuits

Standards for testing at **JEDEC**



ESD in Silicon **Integrated Circuits**

Second Edition

AJITH AMERASEKERA | CHARVAKA DUVVURY

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When do ESD events occur?

Before/during PCB Human body model (HBM)

Charged device model (CDM)

System level ESD

After PCB Human body model (HBM)

Human body model (HBM)

- Models a person touching a device with a finger
- Long duration (around 100 ns)
- Acts like a current source into a pin
- Can usually be handled in the I/O ring
- 4 kV HBM ESD is 2.67 A peak current

1.5 kOhm

100 pF

Imagine a ESD zap between VSS and VDD. How can we protect the device?



An ESD zap example

Permutations

0-+ 1	VSS - V90
1 - 0	vod - vss
0-02	vss - PIN
2 - 0	PIN - Ves
1-02	VOS - PIN
2-1	PIN - 100

D

..... VDP ρW •









Q: Why does this work?

If you don't do the layout right³



Fig. 5. Layout top view of the self-protecting fully silicided I/O buffer in a CMOS IC product.



NMOS without ballasting.

³New Ballasting Layout Schemes to Improve ESD Robustness of I/O Buffers in Fully Silicided CMOS Process

Carsten Wulff 2023

Fig. 6. SEM image of the fully silicided I/O buffer without ballasting after 2-kV PS-mode ESD stress. ESD failure is found on only one finger of the driver NMOS. Current filamentation is also observed on the surface of the driver



Q: How can current in one place lead to a current somewhere else?

You must always handle ESD on an IC

- Do everything yourself
- Use libraries from foundry
- Get help www.sofics.com



